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UG/4th Sem/PHY/19

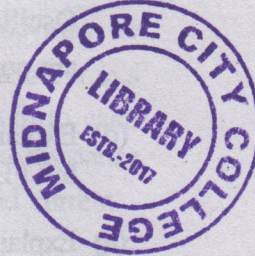
2019

B.Sc. (Hons)

4th Semester Examination

PHYSICS

Paper - C10T



Full Marks : 40

Time : 2 Hours

The figures in the margin indicate full marks.

*Candidates are required to give their answers
in their own words as far as practicable.*

1. Answer any *five* of the following : $2 \times 5 = 10$

(a) Show that the total conductivity of a semi-conductor is $\sigma = e(p\mu_p + n\mu_n)$ where p = density of holes, n = density of electron, μ_p = mobility of hole, μ_n = mobility of electron.

(b) What is ripple factor ? Show that the ripple factor of a half wave rectifier is 1.21.

[Turn Over]

(2)

- (c) Determine the operating frequency of Hartley Oscillator where $L_1 = 1000\mu\text{H}$, $L_2 = 100\mu\text{H}$ are connected in series and $C = 20\text{PF}$.
- (d) Explain — "BJT is a current controlled device but FET is a voltage controlled device".
- (e) Explain how an OPAMP can be used as voltage comparator.
- (f) How does the dynamic resistance (r) of a pn junction depend on forward current ?
- (g) Sketch the variation of space charge, electric field and potential as a function of distance across the junction of an open circuited p-n junction.
- (h) How is the depletion region formed in p-n junction ?

2. Answer any *four* of the following : $5 \times 4 = 20$

- (a) (i) Show that the barrier width of a p-n diode

$$\text{is } W = \sqrt{\frac{2\epsilon V_0}{e} \left(\frac{N_a + N_D}{N_A N_D} \right)}, \text{ symbols}$$

having their usual meaning. $2\frac{1}{2}$

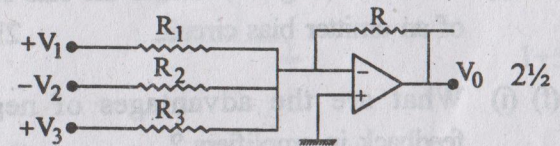
(3)

- (ii) A full wave rectifier use two diodes, the internal resistance of each diode may be assumed at 20Ω . The transformer r.m.s secondary voltage from centre tap to each end of secondary is 50V and load resistance 980Ω . Find mean and r.m.s load current.

$2\frac{1}{2}$

- (b) (i) Explain how an OPAMP can be used as a logarithmic amplifier. $2\frac{1}{2}$

- (ii) Calculate the output voltage of the following circuit



$2\frac{1}{2}$

- (c) (i) Establish the relation

$I_C = \beta J_B + (1 + \beta) I_{CBO}$ for CE transistor in active region, where symbols have usual meaning.

- (ii) Thermal noise in CE circuit is much higher than that in CB circuit. Explain. $3+2$

[Turn Over]

(4)

- (d) Draw a neat diagram of a bridge rectifier. What are its advantages over a full wave rectifier ?

A 6.8V, 300 mW Zener diode is used as voltage regulator with resistance $R_L = 1K\Omega$ and a series resistance $R_s = 220\Omega$.

Find the minimum and maximum values of input voltage for which the output will be maintained constant at 6.8V. 1+1+3

- (e) (i) What do you mean by stability of bias point of a bipolar junction transistor ?

(ii) With neat diagram, discuss the bias stability of an emitter bias circuit. 2½+2½

- (f) (i) What are the advantages of negative feedback in amplifiers ?

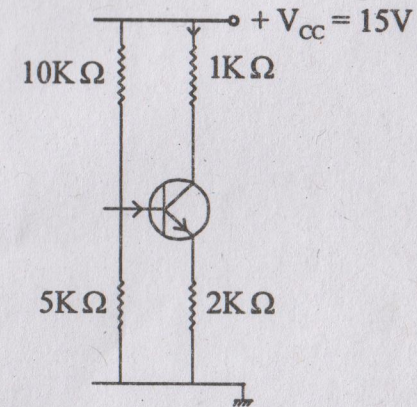
(ii) How are the input and output resistances of an amplifier modified in voltage series feedback ? 2+3

3. Answer any *one* of the following : 10×1=10

- (a) (i) What is differential amplifier ? Draw the circuit of an emitter coupled differential amplifier and explain its operation.

(5)

- (ii) The following figure shows the voltage divider bias method. Draw the D.C load line and determine the operating point. (Assuming the transistor to be of Si)



1+5+4

- (b) Deduce an expression for the voltage gain and phase difference for a lead-lag network. Show that the output is in phase with the input at resonance. Design a Wien bridge oscillator using this network. How is the amplitude of oscillation controlled in the circuit ? 3+2+1+2+2